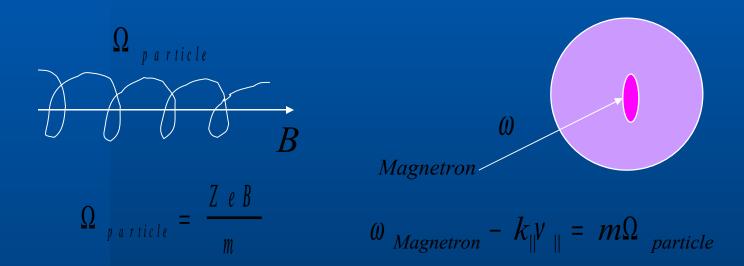
# Construction and Operation of an Electron Cyclotron Resonance Sputter Source

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# Electron Cyclotron Resonance

•Microwave-electron interaction:



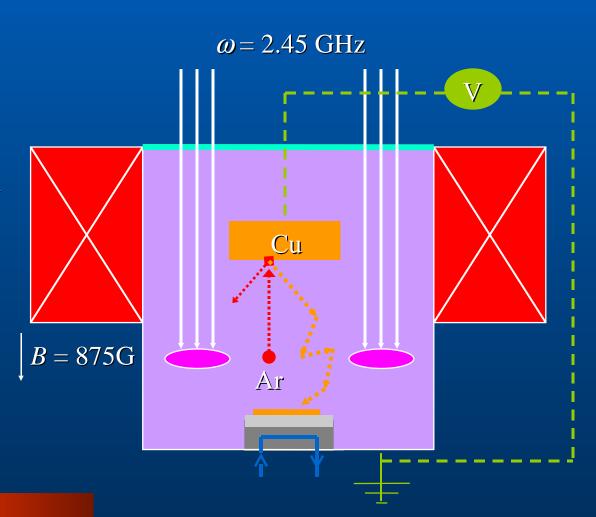
•When microwaves are in phase with particle gyration, the particle experiences an E field and accelerates in the perpendicular direction.

# Benefits of ECR Sputtering

- •ECR systems deposit semiconductor and metal thin films on materials.
- •Optimized deposition of thin films yield smooth surfaces with excellent crystallinity or atom arrangement, and have excellent electrical properties.
- •Films can be deposited without substrate heating, thus sensitive substrates could be used.
- •The thin film materials need not be conducting.
- •Lucrative, rewarding, and novel applications in materials and semiconductor processing.

# ECR Sputtering

- •Microwaves resonate with electrons in B field to heat the plasma.
- •Bias voltage is applied to accelerate plasma (Ar) ions towards the sputtering material (Cu).
- •Argon ions collide with the sputtering material.
- •The sputtering material diffuses into plasma.
- •The sputtering material deposits onto a substrate.

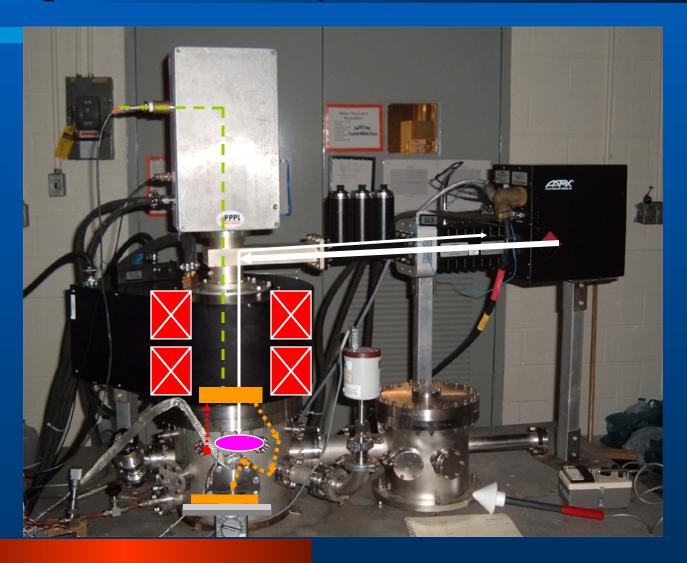


# Experimental System Constructed

- •Constructed in summer of 2003.
- •Stacked magnetic coil confinement scheme (~1kG).
- •5kW capable microwave source.
- •Manual triple-stub microwave impedance tuner.
- •Silica quartz window.



# Experimental System Constructed



# Operational Challenges

### Adequate cooling:

Old manifold (15 minutes of operation):



New manifold (infinite operation):



### Microwave impedance tuning:

Manual triple stub tuner: <30% Reflected power (10 minutes).

Automated tuner (installation pending): <1% Reflected power (1 minute).

•Electrical impedance maximization.

# Operational Challenges (continued)

- •ECR plasma created.
- Achieving optimum plasma parameters:
  - •The ideal plasma location is in the lower vacuum vessel. Plasmas near the silica quartz window can damage window seals.
  - •The ideal pressure is ~1-3mTorr. Pressure regulation is currently achieved using a manual needle valve. It is necessary to install mass-flow controller for precision.
  - •Purity of the plasma was confirmed spectroscopically by comparing plasma spectra to NIST reference spectra of Argon.





# Experimental Challenges

### •Optimization of sputtering:

- •Low sputtering current detected.
- •Non-uniform bias voltage dependence observed.
- •Unknown pressure dependence on sputter yield.
- •Unknown temperature and density profiles.
- •Unknown ion energy distribution and concentrations.

## Future Work

### Operational enhancement:

- •Installation of automatic impedance tuner.
- •Installation of mass-flow controller.

### •Experimental work:

- •Characterization of deposition (profiles, rates).
- •Characterization of plasma parameters.
- •Optimization of substrate (geometry, temperature, voltage biasing).
- •Eventual use of ECR Sputter System as a user facility for research and education.

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